## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet





**SMA** 

#### **FEATURES**

- \* Ideal for surface mount applications
- \* Easy pick and place
- \* Built-in strain relief
- \* Fast switching speed

#### **MECHANICAL DATA**

\* Case: Molded plastic

\* Epoxy: UL 94V-0 rate flame retardant

\* Metallurgically bonded construction

\* Polarity: Color band denotes cathode end

\* Mounting position: Any \* Weight: 0.063 grams

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

TYPE NUMBER	US2A	US2B	US2D	US2E	US2G	US2J	US2K	US2M	UNITS
Maximum Recurrent Peak Reverse Voltage		100	200	300	400	600	800	1000	V
Maximum RMS Voltage		70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage		100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current		•		•	•	•		•	
.375"(9.5mm) Lead Length at Ta=50°C		2.0					Α		
Peak Forward Surge Current, 8.3 ms single half sine-wave									
superimposed on rated load (JEDEC method)				6	0				Α
Maximum Instantaneous Forward Voltage at 2.0A		1.0 1.3 1.85				V			
Maximum DC Reverse Current Ta=25°C				5	.0				μΑ
at Rated DC Blocking Voltage Ta=100°C	150		μА						
Maximum Reverse Recovery Time (Note 1)		50 70				nS			
Typical Junction Capacitance (Note 2)		30				pF			
Operating and Storage Temperature Range Тл, Тэтс		-65—+150					°C		

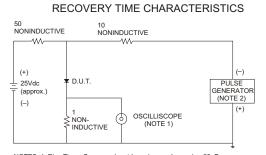
#### NOTES:

- 1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.



FIG.1-TYPICAL FORWARD CHARACTERISTICS 10 INSTANTANEOUS FORWARD CURRENT, (A) 1.0 .1 Pulse Width 300us 1% Duty Cycle .01 .001 .6 .8 1.0 1.2 1.4 1.6 FORWARD VOLTAGE,(V)

FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

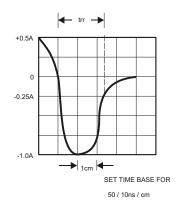


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

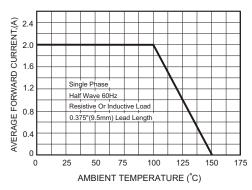


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

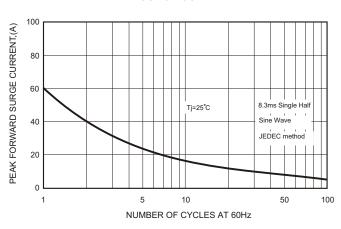
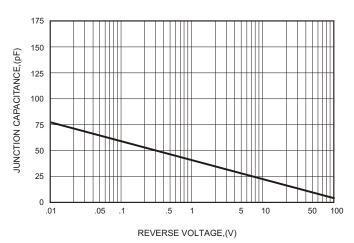
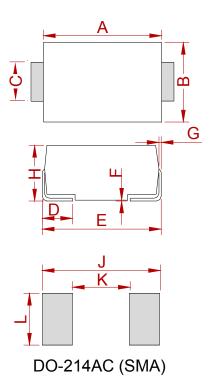


FIG.5-TYPICAL JUNCTION CAPACITANCE





## **PACKAGE MECHANICAL DATA**



	Dimensions					
Ref.	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	4.25	4.65	0.167	0.183		
В	2.50	2.90	0.098	0.114		
С	1.35	1.65	0.053	0.065		
D	0.76	1.52	0.030	0.060		
E	4.93	5.28	0.194	0.208		
F	0.051	0.203	0.002	0.008		
G	0.15	0.31	0.006	0.012		
Н	1.98	2.41	0.078	0.095		
J	6.50		0.256			
K		2.30		0.090		
L	1.70		0.067			

### **REEL SPECIFICATION**

P/N	PKG	QTY
US2A THRU US2M	SMA	2000



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